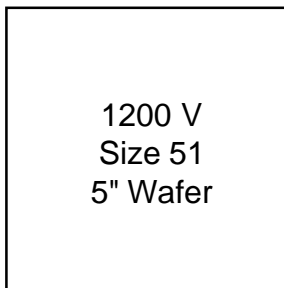


HF51C120ACE

Hexfred Die in Wafer Form



Electrical Characteristics (Wafer Form)

Parameter	Description	Guaranteed (Min/Max)	Test Conditions
V _{FM}	Forward Voltage	3V Max.	T _J = 25°C, I _F = 16A
BV _R	Reverse Breakdown Voltage	1200V Min.	T _J = 25°C, I _R = 200μA
I _{RM}	Reverse Leakage Current	20μA Max.	T _J = 25°C, V _R = 1200V

Mechanical Data

Nominal Back Metal Composition, Thickness	Cr-Ni-Ag (1kA-4kA-6kA)
Nominal Front Metal Composition, Thickness	99% Al, 1% Si (3 microns)
Chip Dimensions	0.340" x 0.195"
Wafer Diameter	125mm, with std. < 100 > flat
Wafer Thickness	.015" ± .003"
Relevant Die Mechanical Dwg. Number	01-5172
Minimum Street Width	100 Microns
Reject Ink Dot Size	0.25mm Diameter Minimum
Recommended Storage Environment	Store in original container, in dessicated nitrogen, with no contamination

Reference Standard IR packaged part (for design) : HFA30PB120

Die Outline

